

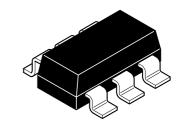
ZXTC2045E6

Dual 40V complementary transistors in SOT23-6

Summary

 $BV_{CEV} = 40V$

 $BV_{CEO} = 30V$

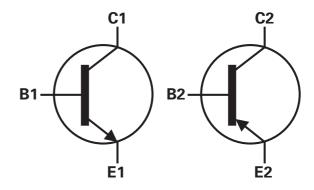


Features

- 40V complementary device
- Up to 5 amps peak current
- High h_{FE}
- SOT236 package

Applications

· MOSFET and IGBT gate driving



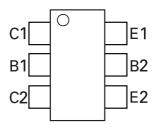
Ordering information

Device	Reel size	Tape width	Quantity per reel
ZXTC2045E6TA	7"	8mm embossed	3,000
ZXTC2045E6TC	13"	8mm embossed	10,000

Device marking

2045

Pin out - top view



Absolute maximum ratings (each transistor)

Parameter	Symbol	Limit		Unit
		NPN	PNP	
Collector-base voltage	BV _{CBO}	40	-40	V
Collector-emitter voltage	BV _{CEV}	40	-40	V
Collector-emitter voltage	BV _{CEO}	30	-30	V
Emitter-base voltage	BV _{EBO}	7	-7	V
Peak pulse current	I _{CM}	5	-5	А
Continuous collector current (a)	I _C	1.5	-1.5	Α
Base current	I _B	1	-1	А
Power dissipation at T _A =25°C ^{(a) (c)} Linear derating factor	P _D	0.9 7.2		W mW/°C
Power dissipation at T _A =25°C ^{(a) (d)} Linear derating factor	P _D	1.1 8.8		W mW/°C
Power dissipation at T _A =25°C ^{(b) (c)} Linear derating factor	P _D	1.7 13.6		W mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to	+150	°C

Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient ^{(a) (c)}	$R_{ heta JA}$	139	°C/W
Junction to ambient (b) (c)	$R_{\theta JA}$	73	°C/W
Junction to ambient ^{(a) (d)}	$R_{ heta JC}$	113	°C/W

NOTES:

⁽a) For a device surface mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

⁽b) As above measured at t < 5 seconds.

⁽c) For device with one active die.

⁽d) For device with two active dice running at equal power.

Electrical characteristics (at T_{AMB} = 25°C unless otherwise stated)

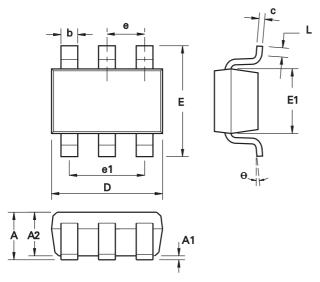
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	(-)40 ^(*)			V	I _C = (-)100μA
Collector-emitter breakdown voltage	BV _{CEV}	(-)40 ^(*)			V	$I_C = (-)1\mu A$ $0.25V > V_{BE} > 1.0V$ $(0.25V < V_{BE} < 1.0V)$
Collector-emitter breakdown voltage	BV _{CEO}	(-)30 ^(*)			V	I _C = (-)10mA ^(†)
Emitter-base breakdown voltage	BV _{EBO}	(-)7 ^(*)	(-)8.5 ^(*)		V	I _E = (-)100μA
Collector cut-off current	I _{CBO}		(-)<1 ^(*)	(-)20 ^(*)	nA	V _{CB} = (-)32V
Collector cut-off current	I _{CES/R}		(-)<1 ^(*)	(-)20 ^(*)	nA	V_{CE} = (-)16V, R \leq 1k Ω
Emitter cut-off current	I _{EBO}		(-)<1 ^(*)	(-)20 ^(*)	nA	V _{EB} = (-)6V
Collector-emitter saturation voltage	V _{CE(SAT)}			(-)375 ^(*)	mV	$I_C = (-)0.75A, I_B = (-)15mA^{(\dagger)}$
Base-emitter saturation voltage	V _{BE(SAT)}			(-)1.2 ^(*)	V	I _C =(-) 0.75A, I _B =(-)15mA ^(†)
Static forward current transfer ratio	h _{FE}	180	300	500		$I_C = (-)100 \text{mA}, V_{CE} = (-)2V^{(\dagger)}$

NOTES:

^{(*)()} applies to PNP

^(†) Measured under pulsed conditions. Pulse width \leq 300 s; duty cycle \leq 2%.

Package details - SOT23-6



DIM	Millimeters		Inc	Inches	
	Min.	Max.	Min.	Max.	
А	0.90	1.45	0.354	0.0570	
A1	0.00	0.15	0.00	0.0059	
A2	0.90	1.30	0.0354	0.0511	
b	0.35	0.50	0.0078	0.0196	
С	0.09	0.26	0.0035	0.0102	
D	2.70	3.10	0.1062	0.1220	
Е	2.20	3.20	0.0866	0.1181	
E1	1.30	1.80	0.0511	0.0708	
L	0.10	0.60	0.0039	0.0236	
е	0.95 REF		0.0374 REF		
e1	1.90 REF		0.074	8 REF	
L	0°	30°	0°	30°	

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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